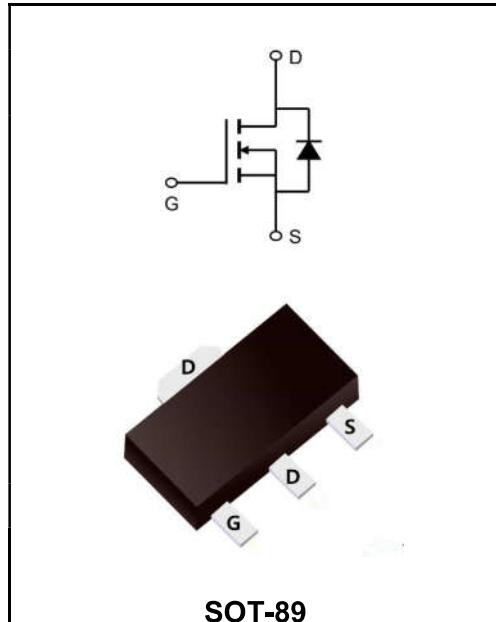


60V N-CHANNEL ENHANCEMENT MODE MOSFET
MAIN CHARACTERISTICS

I_D	4.8A
V_{DSS}	60V
$R_{DS(on)-typ}(@V_{GS}=10V)$	< 95mΩ (Type: 72 mΩ)


Application

- ◆ Battery protection
- ◆ Load switch
- ◆ Uninterruptible power supply

Marking Code

YFW4N06SI	YFW4N06SI
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Maximum Ratings at $T_c=25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbols	Value	Units
Drain-Source Voltage	V_{DS}	60	V
Gate - Source Voltage	V_{GS}	± 20	V
Continuous Drain Current, $V_{GS} @ 10V^1$ @ $T_c=25^\circ\text{C}$	I_D	4.8	A
Continuous Drain Current, $V_{GS} @ 10V^1$ @ $T_c=100^\circ\text{C}$	I_D	2.0	A
Pulsed Drain Current ²	I_{DM}	15	A
Single Pulse Avalanche Energy ³	E_{AS}	6.2	mJ
Total Power Dissipation ⁴ @ $T_c=25^\circ\text{C}$	P_D	1.5	W
Storage Temperature Range	T_{STG}	-55 to +150	°C
Operating Junction Temperature Range	T_J	-55 to +150	°C
Thermal Resistance, Junction-to-Ambient ¹	$R_{\theta JA}$	85	°C/W
Thermal Resistance Junction-Case ¹	$R_{\theta JC}$	48	°C/W

Maximum Ratings at T_c=25°C unless otherwise specified

Characteristics	Test Condition	Symbols	Min	Typ	Max	Units
Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	BV _{DSS}	60	65	-	V
BVDSS Temperature Coefficient	Reference to 25°C , I _D =1mA	ΔBV _{DSS/ΔTJ}	-	0.054	-	V/°C
Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =2A	R _{DS(ON)}	-	72	95	mΩ
	V _{GS} =4.5V, I _D =1A		-	85	100	
Gate -Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	V _{GS(th)}	1.2	1.5	2.5	V
VGS(th) Temperature Coefficient		ΔV _{GS(th)}	-	-4.96	-	mV/°C
Drain-Source Leakage Current	V _{DS} =48V , V _{GS} =0V , T _J =25°C	I _{DSS}	-	-	1	μA
	V _{DS} =48V , V _{GS} =0V , T _J =55°C		-	-	5	
Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	I _{GSS}	-	-	±100	nA
Forward Transconductance	V _{DS} =5V, I _D =2A	g _{FS}	-	13	-	S
Total Gate Charge(4.5V)	V _{DS} =48V V _{GS} =4.5V I _D =2A	Q _g	-	5	7.0	nC
Gate-Source Charge		Q _{gs}	-	1.68	2.4	
Gate-Drain Charge		Q _{gd}	-	1.9	2.7	
Turn-on delay time	V _{DD} =30V V _{GS} =10V R _G =3.3Ω I _D =2A	t _{d(on)}	-	1.6	3.2	ns
Rise Time		T _r	-	7.2	13	
Turn-Off Delay Time		t _{d(OFF)}	-	25	50	
Fall Time		t _f	-	14.4	28.8	
Input Capacitance	V _{DS} =15V V _{GS} =0V f=1.0MHz	C _{iss}	-	511	715	pF
Output Capacitance		C _{oss}	-	38	53	
Reverse Transfer Capacitance		C _{rss}	-	25	35	
Continuous Source Current ^{1,4}	V _G =V _D =0V , Force Current	I _s	-	-	2.3	A
Pulsed Source Current ^{2,4}		I _{SM}	-	-	9.2	A
Diode Forward Voltage ²	V _{GS} =0V , I _s =1A , T _J =25°C	V _{SD}	-	-	1.2	V
Reverse Recovery Time	I _F =2A , dI/dt=100A/μs , T _J =25°C	t _{rr}	-	9.7	-	ns
Reverse Recovery Charge		Q _{rr}	-	5.8	-	nC

Note :

- 1、The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3、The EAS data shows Max. rating . The test condition is V DD =25V,V GS =10V,L=0.1mH,IAS =2A
- 4、The power dissipation is limited by 150°C junction temperature
- 5、The data is theoretically the same as I D and I DM , in real applications , should be limited by total power dissipation.

Ratings and Characteristic Curves

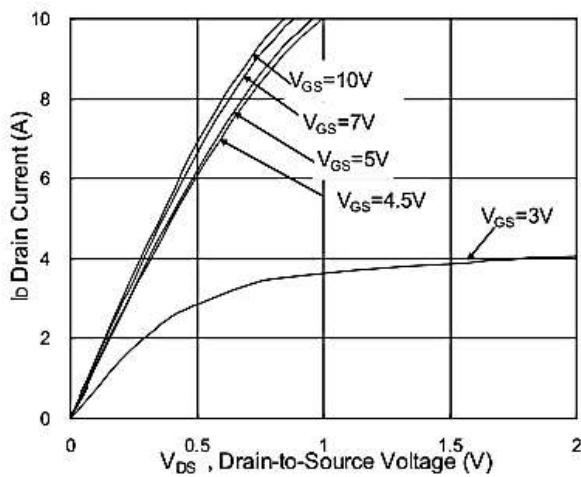


Fig.1 Typical Output Characteristics

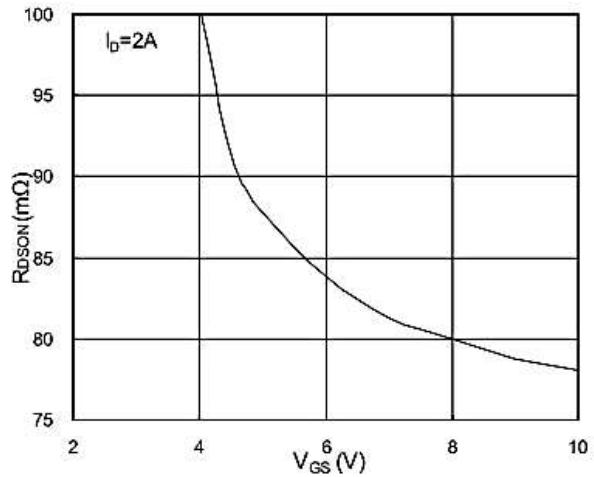


Fig.2 On-Resistance v.s Gate-Source

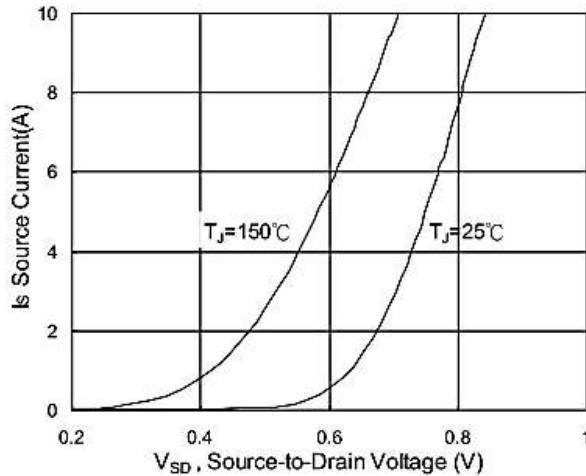


Fig.3 Forward Characteristics of Reverse

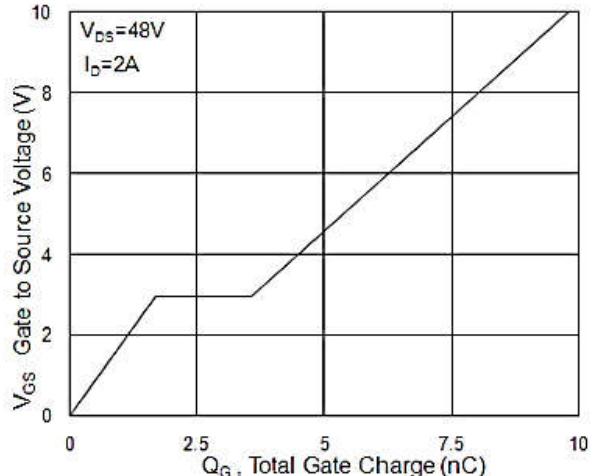


Fig.4 Gate-Charge Characteristics

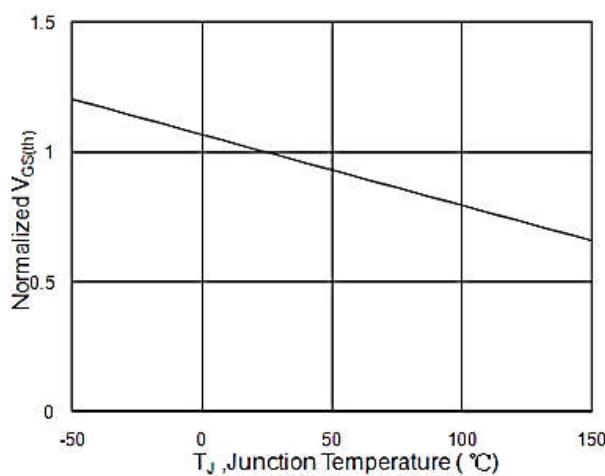


Fig.5 Normalized V_{gs(th)} v.s T_j

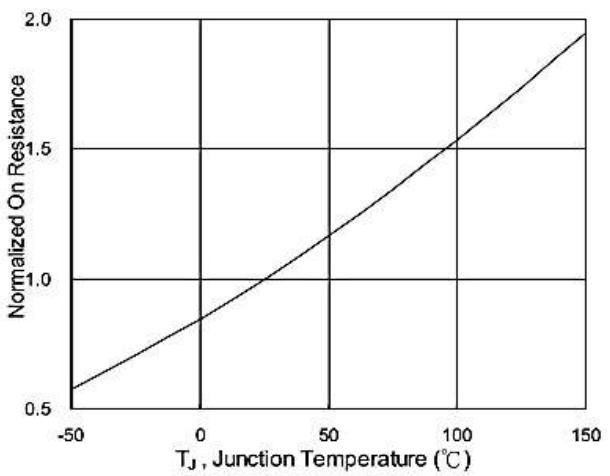


Fig.6 Normalized R_{DSON} v.s T_j

Ratings and Characteristic Curves

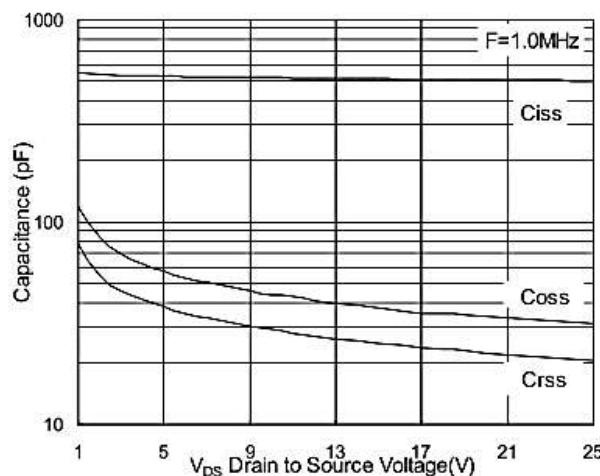


Fig.7 Capacitance

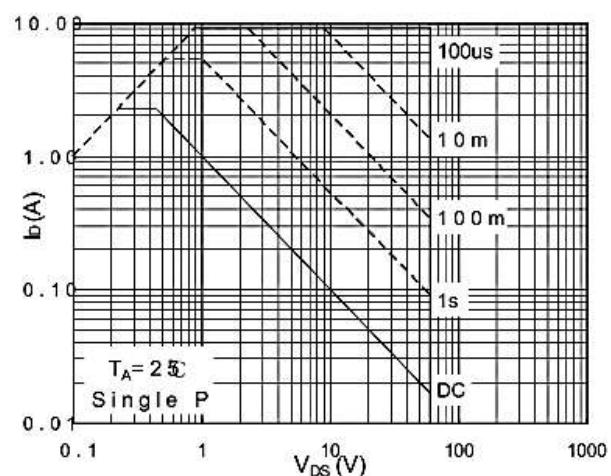


Fig.8 Safe Operating Area

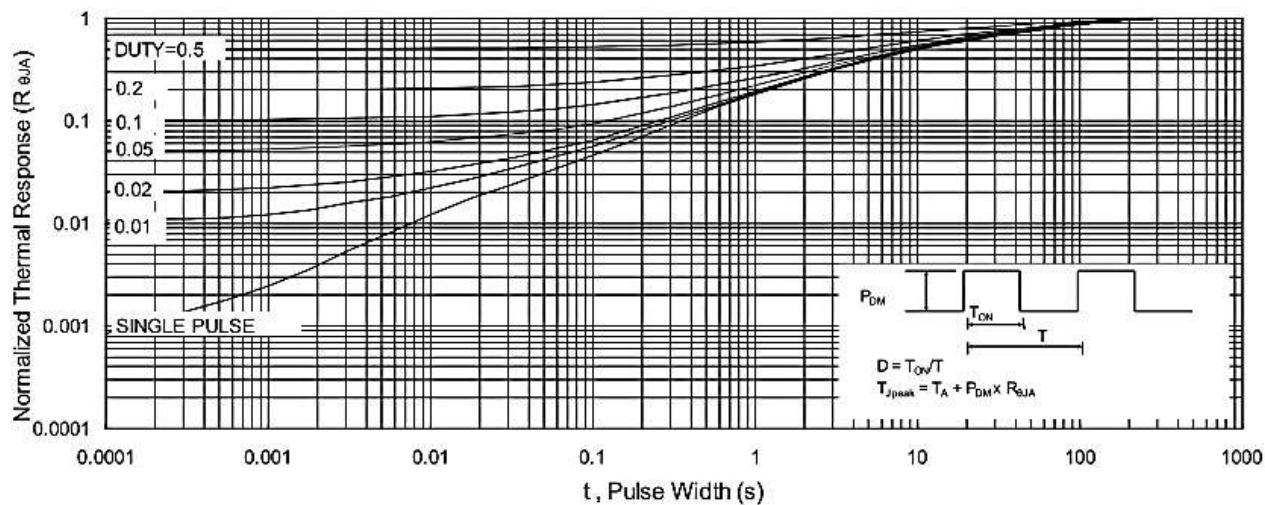


Fig.9 Normalized Maximum Transient Thermal Impedance

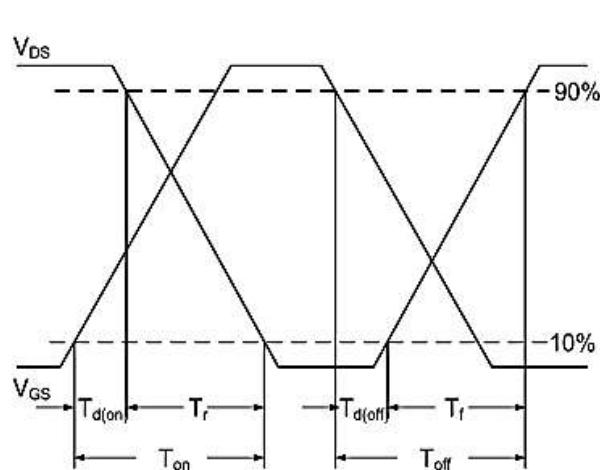


Fig.10 Switching Time Waveform

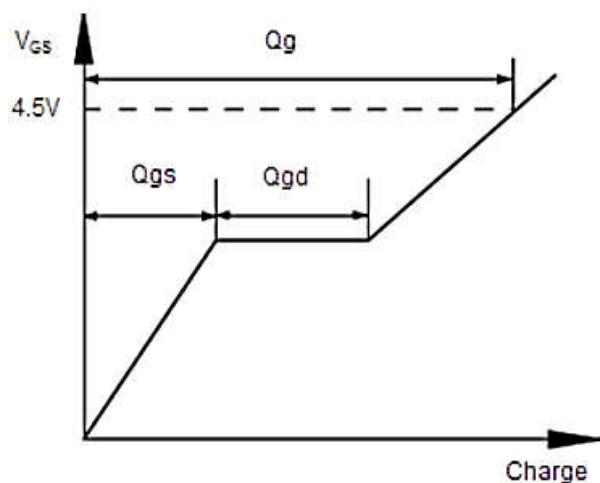
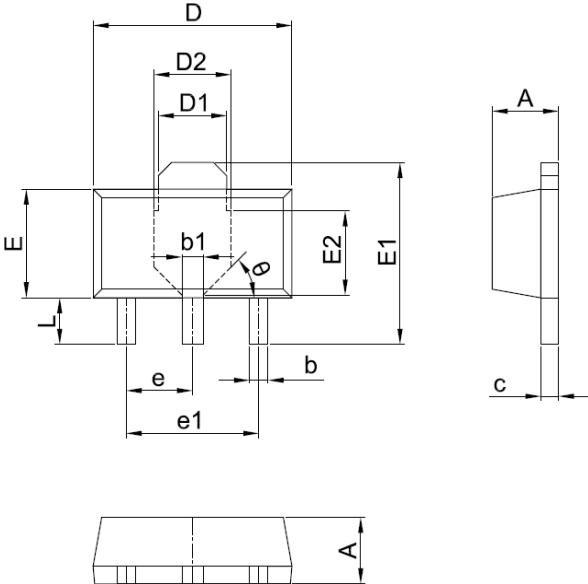


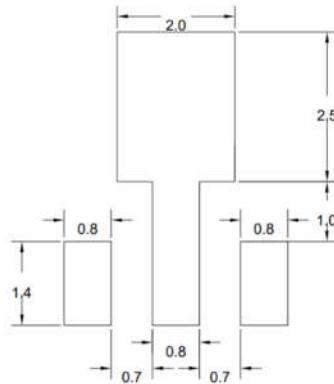
Fig.11 Gate Charge Waveform

Ordering information

Package	Packing Description	Base Quantity	Packing Quantity
SOT-89	Tape/Reel,7"reel	1000pcs/Reel	6000PCS/Box 30000PCS/Carton

Package Dimensions
SOT-89


Dim	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	1.40	1.60	0.055	0.063
b	0.32	0.52	0.013	0.020
b1	0.38	0.58	0.015	0.023
c	0.35	0.45	0.014	0.018
D	4.40	4.60	0.173	0.181
D1	1.45	1.65	0.057	0.065
D2	1.70	1.80	0.067	0.071
E	2.30	2.60	0.091	0.102
E1	3.95	4.25	0.156	0.167
E2	1.80	2.00	0.071	0.079
e	1.40	1.60	0.055	0.063
e1	2.80	3.20	0.110	0.126
L	0.90	1.20	0.035	0.047

The recommended mounting pad size

UNIT:MM

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